

TPCA8107-H

High Efficiency DC/DC Converter Applications

Notebook PC Applications

Portable Equipment Applications

CCFL Inverter Applications

- Small footprint due to a small and thin package
- High speed switching
- Small gate charge: $Q_{SW} = 9.7 \text{ nC}$ (typ.)
- Low drain-source ON-resistance: $R_{DS(ON)} = 24 \text{ m}\Omega$ (typ.)
- High forward transfer admittance: $|Y_{fs}| = 14 \text{ S}$ (typ.)
- Low leakage current: $I_{DSS} = -10 \text{ }\mu\text{A}$ (max) ($V_{DS} = -40 \text{ V}$)
- Enhancement mode: $V_{th} = -0.8 \text{ to } -2.0 \text{ V}$ ($V_{DS} = -10 \text{ V}$, $I_D = -1 \text{ mA}$)

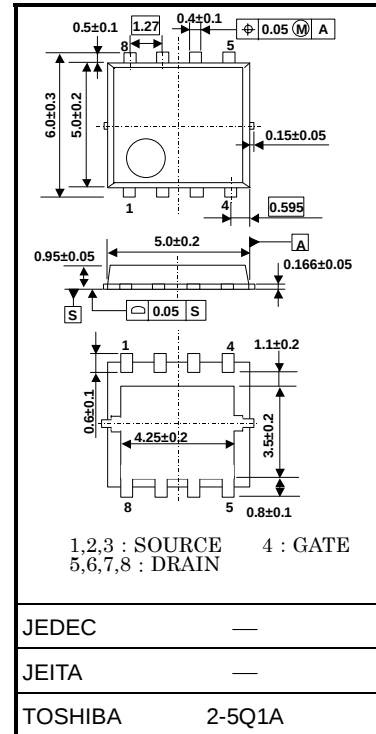
Maximum Ratings ($T_a = 25^\circ\text{C}$)

Characteristic		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	-40	V
Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$)		V_{DGR}	-40	V
Gate-source voltage		V_{GSS}	± 20	V
Drain current	DC (Note 1)	I_D	-7.5	A
	Pulsed (Note 1)	I_{DP}	-30	
Drain power dissipation ($T_c = 25^\circ\text{C}$)		P_D	30	W
Drain power dissipation ($t = 10 \text{ s}$) (Note 2a)		P_D	2.8	W
Drain power dissipation ($t = 10 \text{ s}$) (Note 2b)		P_D	1.6	W
Single-pulse avalanche energy (Note 3)		E_{AS}	26	mJ
Avalanche current		I_{AR}	-7.5	A
Repetitive avalanche energy (Note 2a) (Note 4)		E_{AR}	1.9	mJ
Channel temperature		T_{ch}	150	$^\circ\text{C}$
Storage temperature range		T_{stg}	-55 to 150	$^\circ\text{C}$

Note: For Notes 1 to 4, refer to the next page.

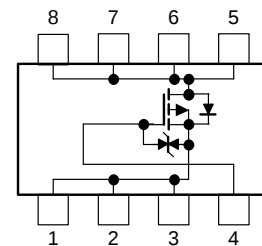
This transistor is an electrostatic-sensitive device. Handle with care.

Unit: mm



Weight: 0.066 g (typ.)

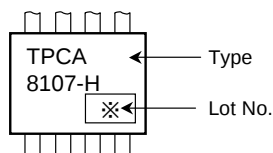
Circuit Configuration



Thermal Characteristics

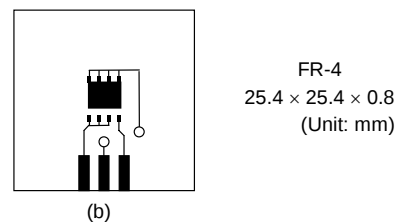
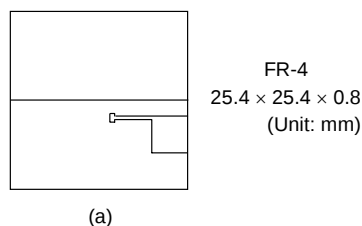
Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case ($T_c=25^{\circ}\text{C}$)	$R_{th(ch-c)}$	4.17	$^{\circ}\text{C/W}$
Thermal resistance, channel to ambient ($t = 10\text{ s}$) (Note 2a)	$R_{th(ch-a)}$	44.6	$^{\circ}\text{C/W}$
Thermal resistance, channel to ambient ($t = 10\text{ s}$) (Note 2b)	$R_{th(ch-a)}$	78.1	$^{\circ}\text{C/W}$

Marking (Note 5)



Note 1: The channel temperature should not exceed 150°C during use.

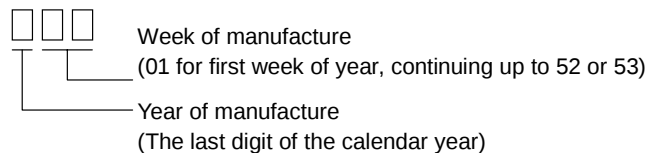
Note 2: (a) Device mounted on a glass-epoxy board (a) (b) Device mounted on a glass-epoxy board (b)



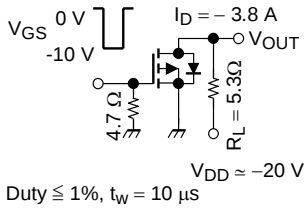
Note 3: $V_{DD} = -24\text{ V}$, $T_{ch} = 25^{\circ}\text{C}$ (initial), $L = 0.5\text{ mH}$, $R_G = 25\ \Omega$, $I_{AR} = -7.5\text{ A}$

Note 4: Repetitive rating: pulse width limited by max channel temperature

Note 5: * Weekly code: (Three digits)

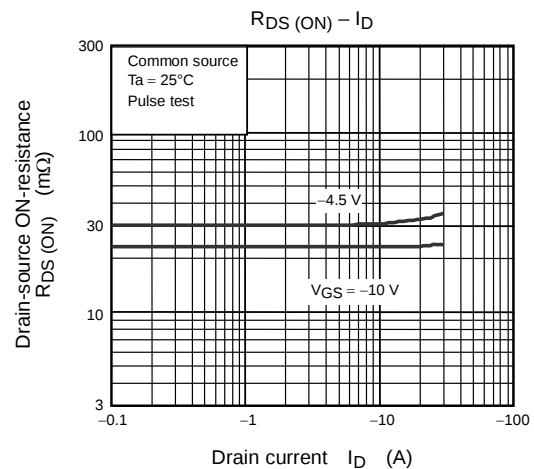
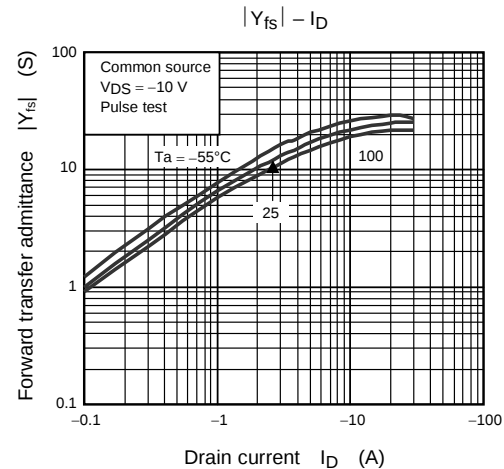
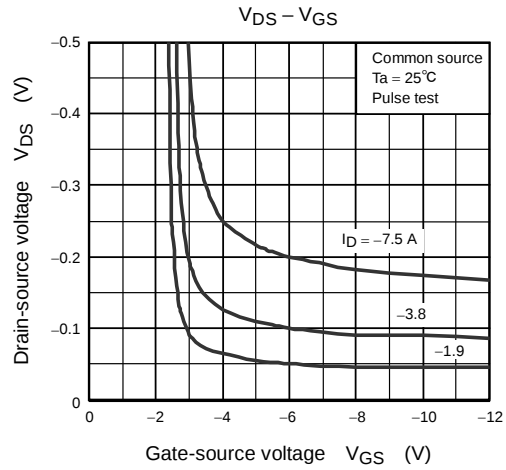
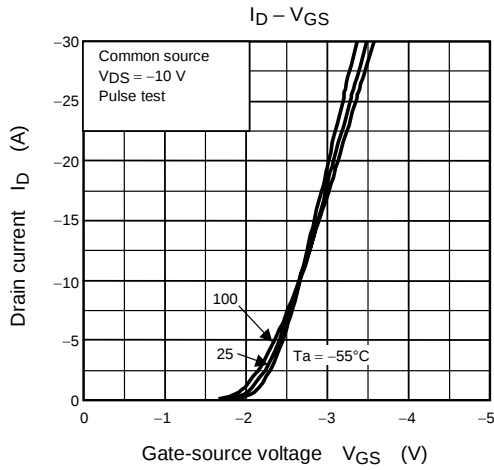
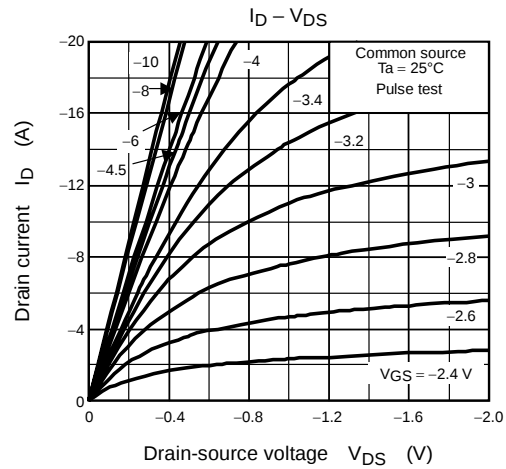
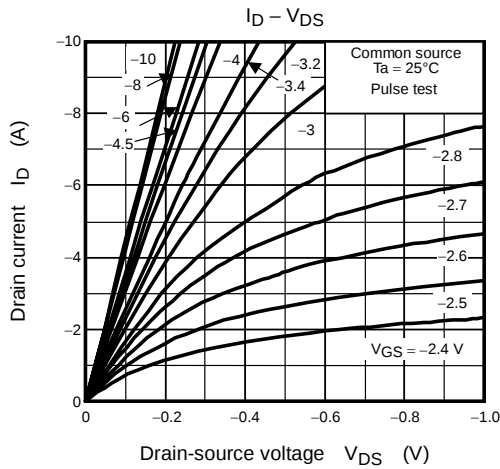


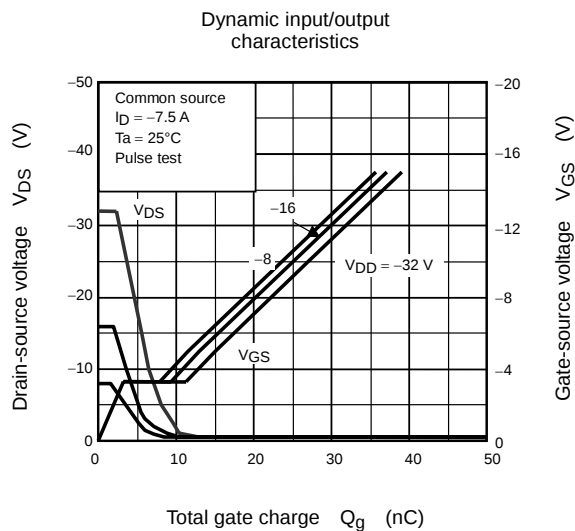
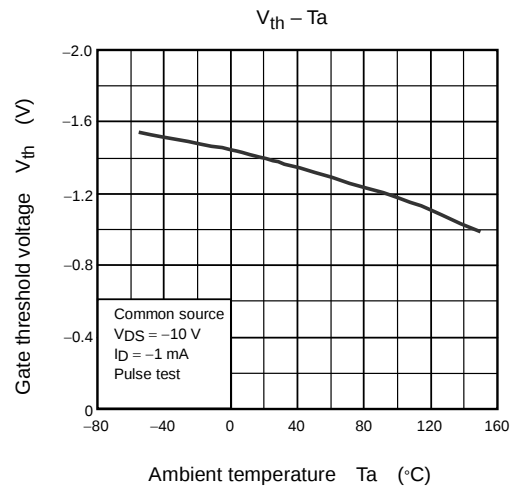
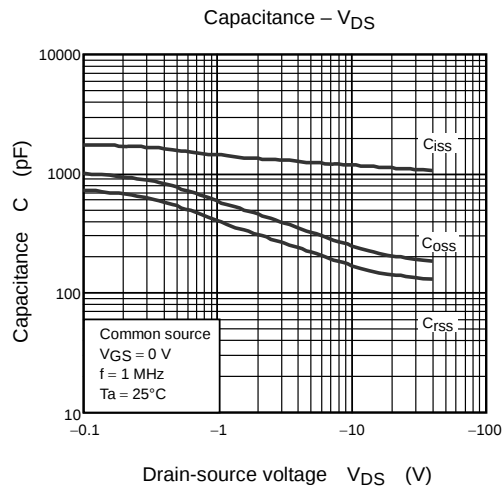
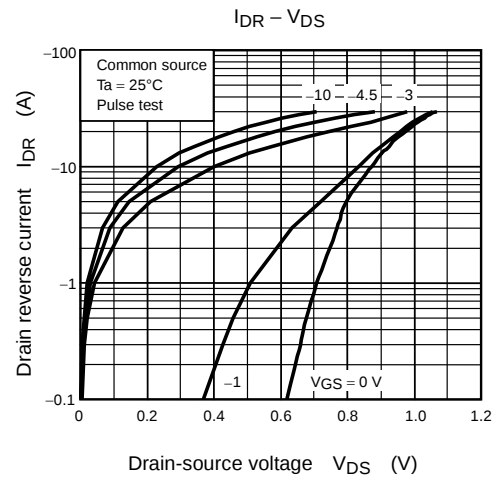
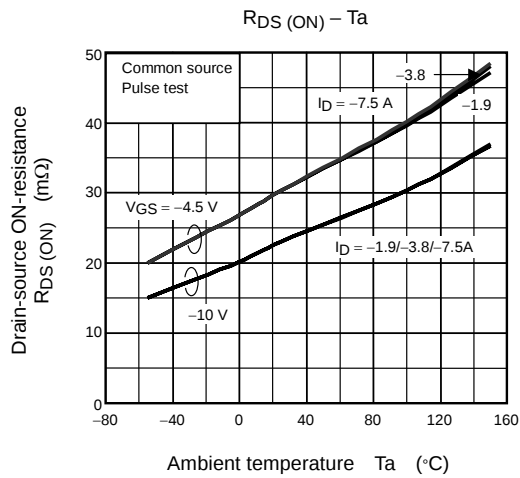
Electrical Characteristics (Ta = 25°C)

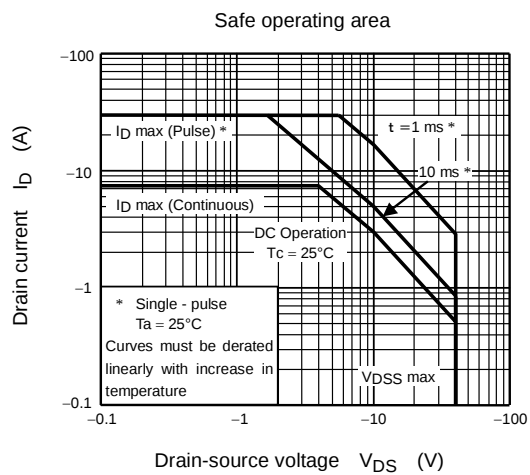
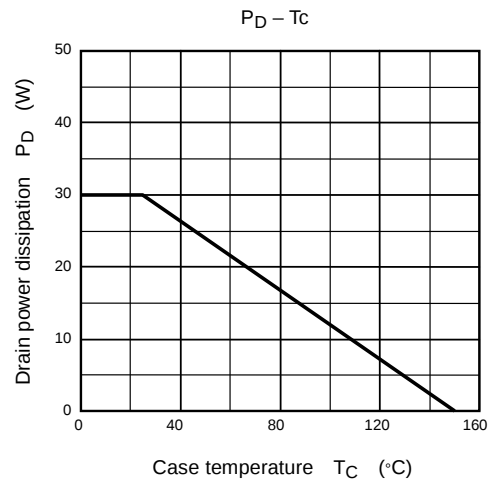
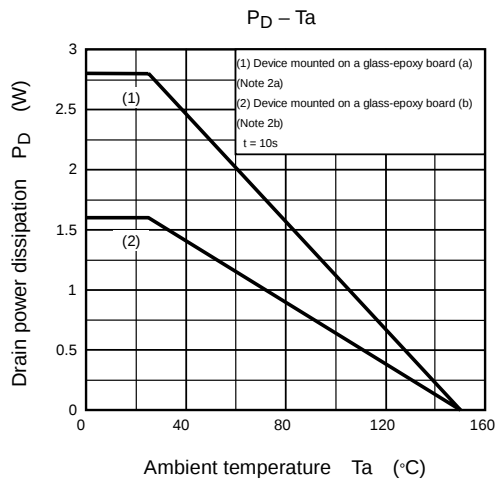
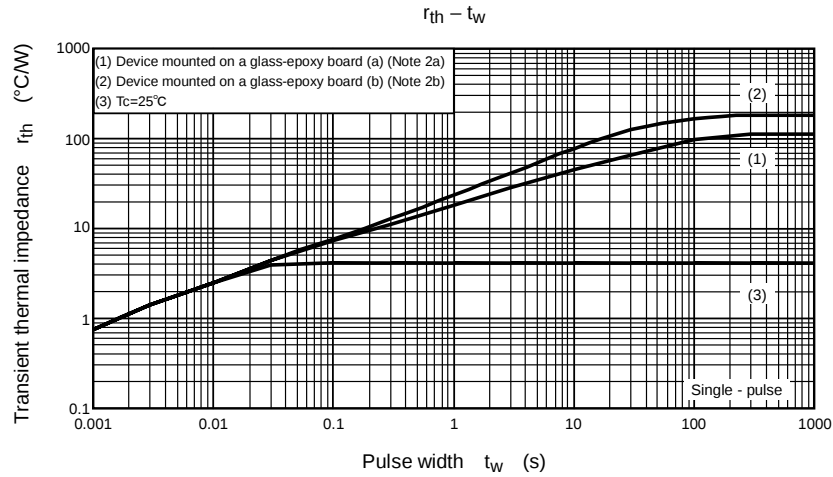
Characteristic		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I _{GSS}	V _{GS} = ±16 V, V _{DS} = 0 V	—	—	±10	μA
Drain cutoff current		I _{DSS}	V _{DS} = -40 V, V _{GS} = 0 V	—	—	-10	μA
Drain-source breakdown voltage		V (BR) DSS	I _D = -10 mA, V _{GS} = 0 V	-40	—	—	V
		V (BR) DSX	I _D = -10 mA, V _{GS} = 20 V	-20	—	—	
Gate threshold voltage		V _{th}	V _{DS} = -10 V, I _D = -1 mA	-0.8	—	-2.0	V
Drain-source ON-resistance		R _{DS (ON)}	V _{GS} = -4.5 V, I _D = - 3.8 A	—	29	37	mΩ
			V _{GS} = -10 V, I _D = - 3.8 A	—	24	30	
Forward transfer admittance		Y _{fs}	V _{DS} = -10 V, I _D = - 3.8 A	7	14	—	S
Input capacitance		C _{iss}	V _{DS} = -10 V, V _{GS} = 0 V, f = 1 MHz	—	1190	—	pF
Reverse transfer capacitance		C _{rss}		—	170	—	
Output capacitance		C _{oss}		—	250	—	
Switching time	Rise time	t _r	 V_{GS} 0 V -10 V I_D = - 3.8 A V_{OUT} 4.7Ω 5.3Ω R_L = 5.3Ω V_{DD} ≈ -20 V Duty ≤ 1%, t_w = 10 μs	—	5	—	ns
	Turn-on time	t _{on}		—	12	—	
	Fall time	t _f		—	12	—	
	Turn-off time	t _{off}		—	43	—	
Total gate charge (gate-source plus gate-drain)		Q _g	V _{DD} ≈ -32 V, V _{GS} = -10V I _D = -7.5A	—	27	—	nC
			V _{DD} ≈ -32 V, V _{GS} = -5 V I _D = - 7.5A	—	15	—	
Gate-source charge 1		Q _{gs1}	V _{DD} ≈ -32 V, V _{GS} = -10 V I _D = - 7.5A	—	3.2	—	
Gate-drain ("Miller") charge		Q _{gd}		—	8.1	—	
Gate switch charge		Q _{sw}		—	9.7	—	

Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Condition	Min	Typ.	Max	Unit
Drain reverse current	Pulse (Note 1)	I_{DRP}	—	—	—	-30	A
Forward voltage (diode)		V_{DSF}	$I_{DR} = -7.5 \text{ A}, V_{GS} = 0 \text{ V}$	—	—	1.2	V







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